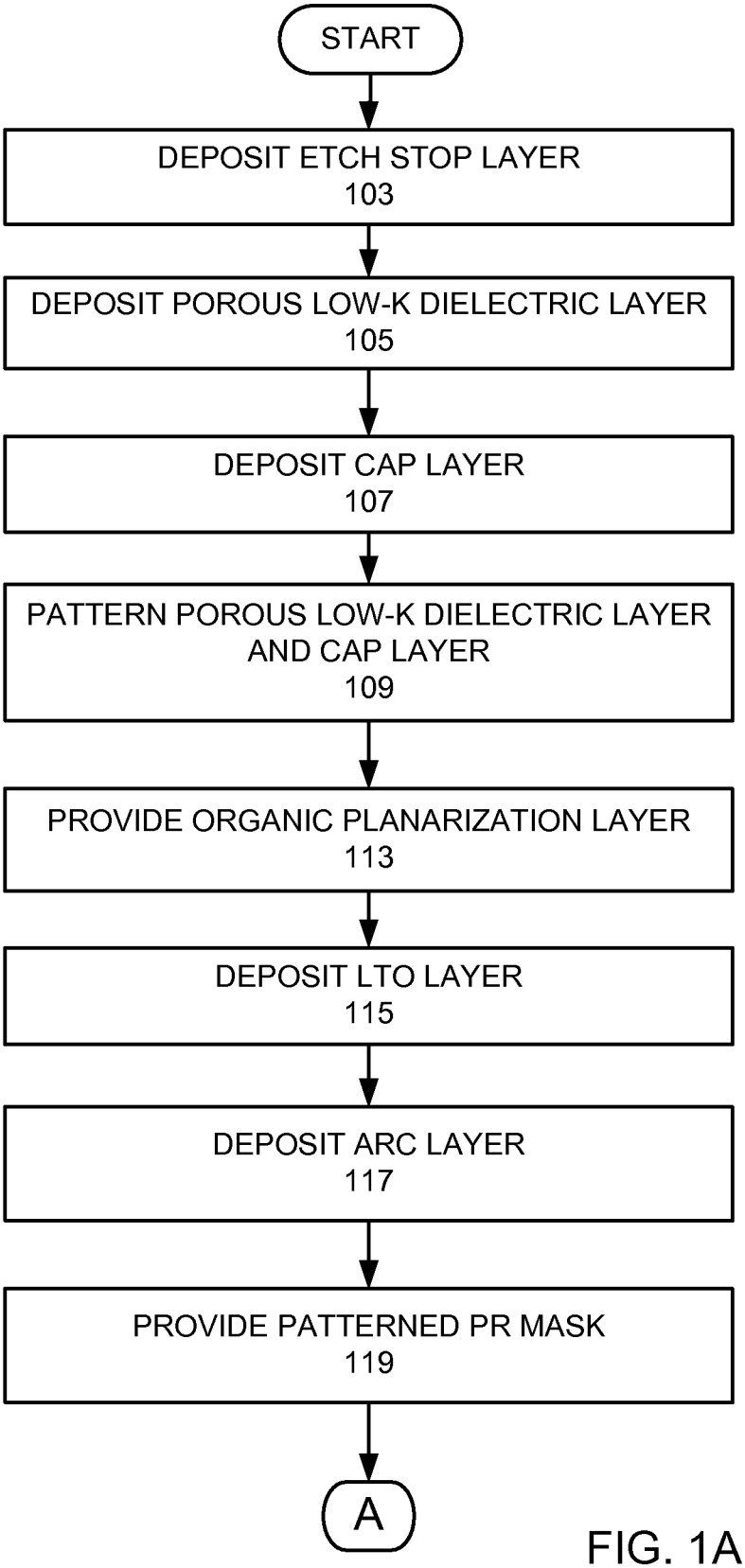

START
DEPOSIT ETCH STOP LAYER
103
DEPOSIT POROUS LOW-K DIELECTRIC LAYER
105
DEPOSIT CAP LAYER
107
PATTERN POROUS LOW-K DIELECTRIC LAYER
AND CAP LAYER
109
PROVIDE ORGANIC PLANARIZATION LAYER
113
DEPOSIT LTO LAYER
115
DEPOSIT ARC LAYER
117
PROVIDE PATTERNED PR MASK
119
A

FIG. 1A

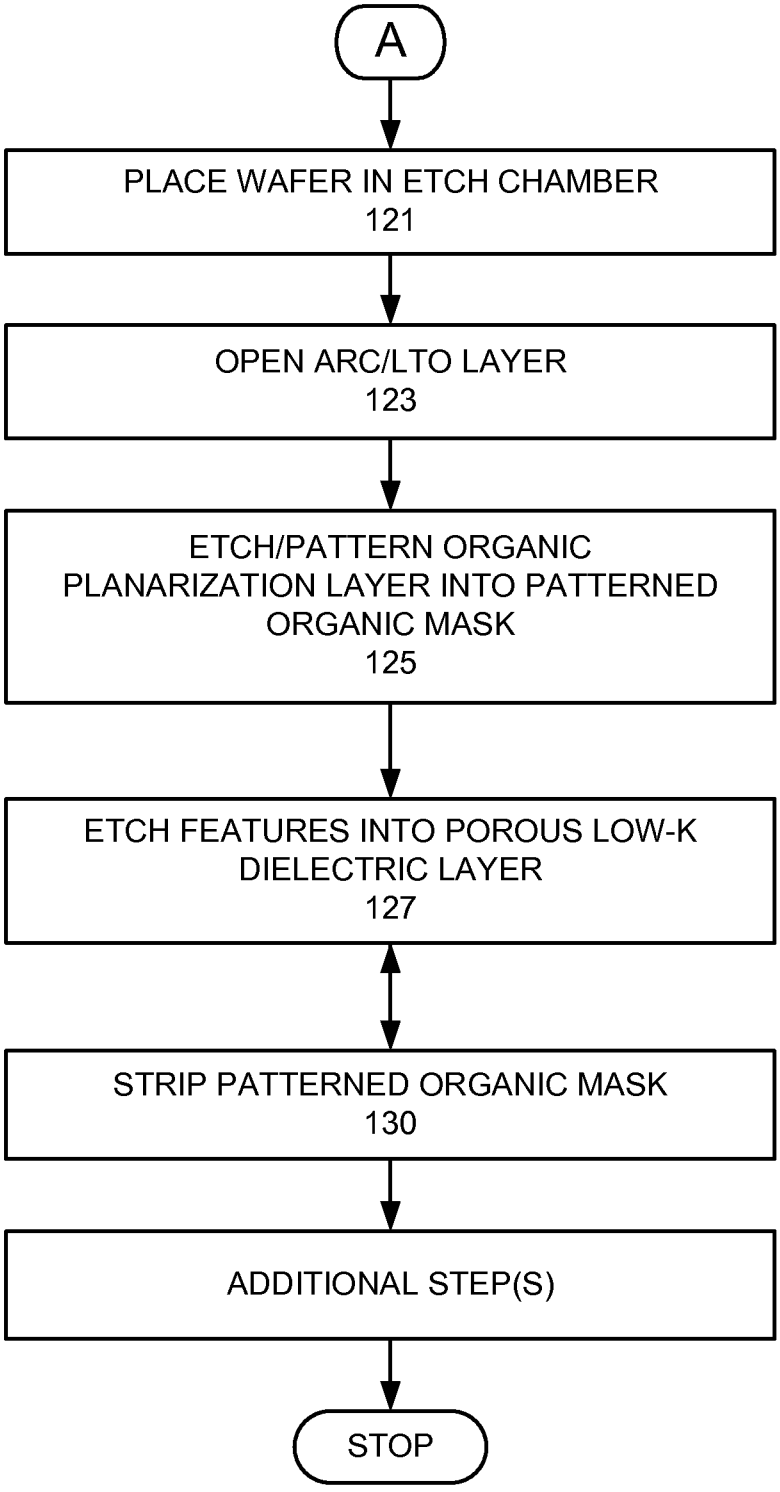

A
PLACE WAFER IN ETCH CHAMBER
121
OPEN ARC/LTO LAYER
123
ETCH/PATTERN ORGANIC PLANARIZATION LAYER INTO PATTERNED ORGANIC MASK
125
ETCH FEATURES INTO POROUS LOW-K DIELECTRIC LAYER
127
STRIP PATTERNED ORGANIC MASK
130
ADDITIONAL STEP(S)
STOP

FIG. 1B

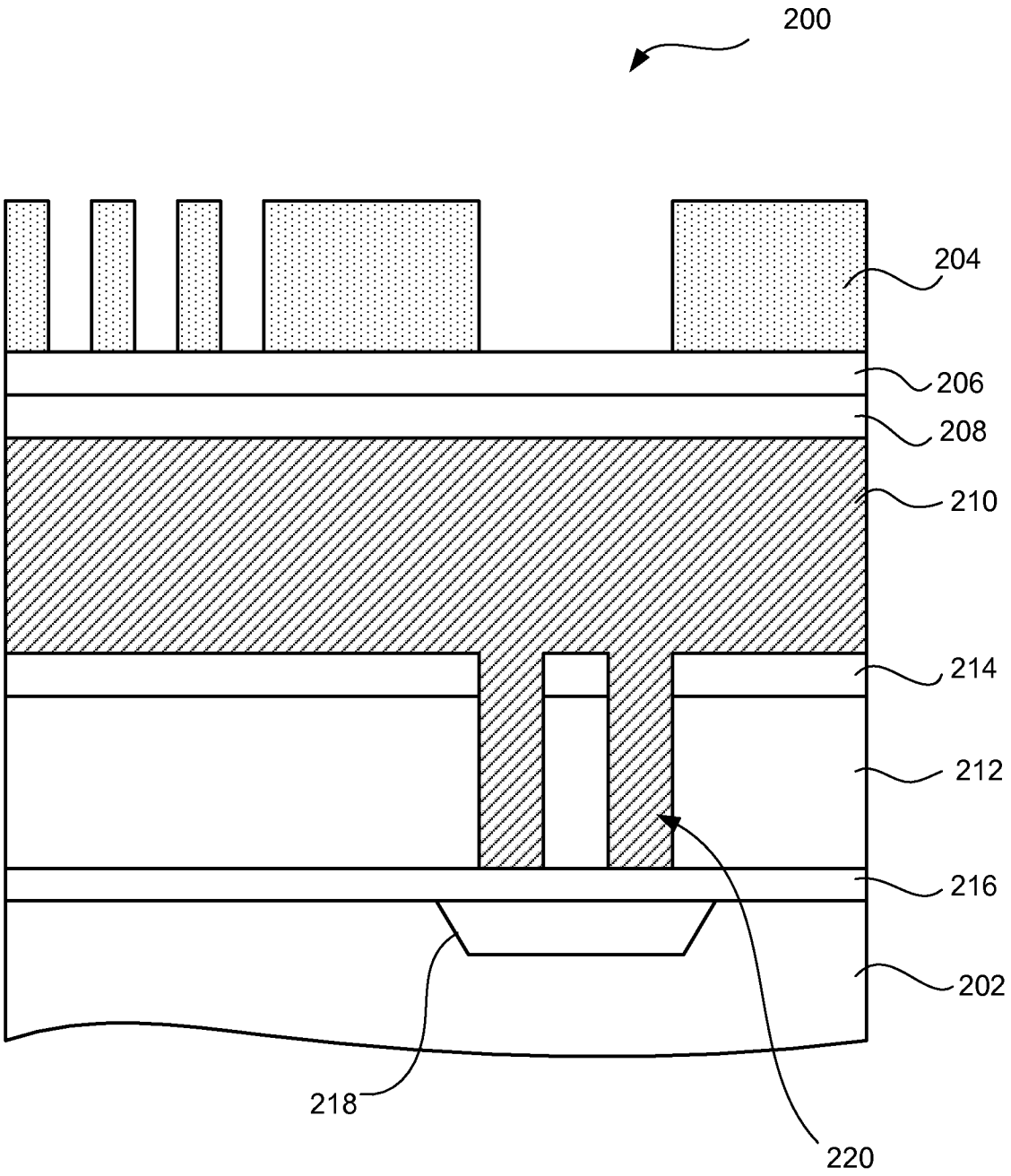


FIG. 2A

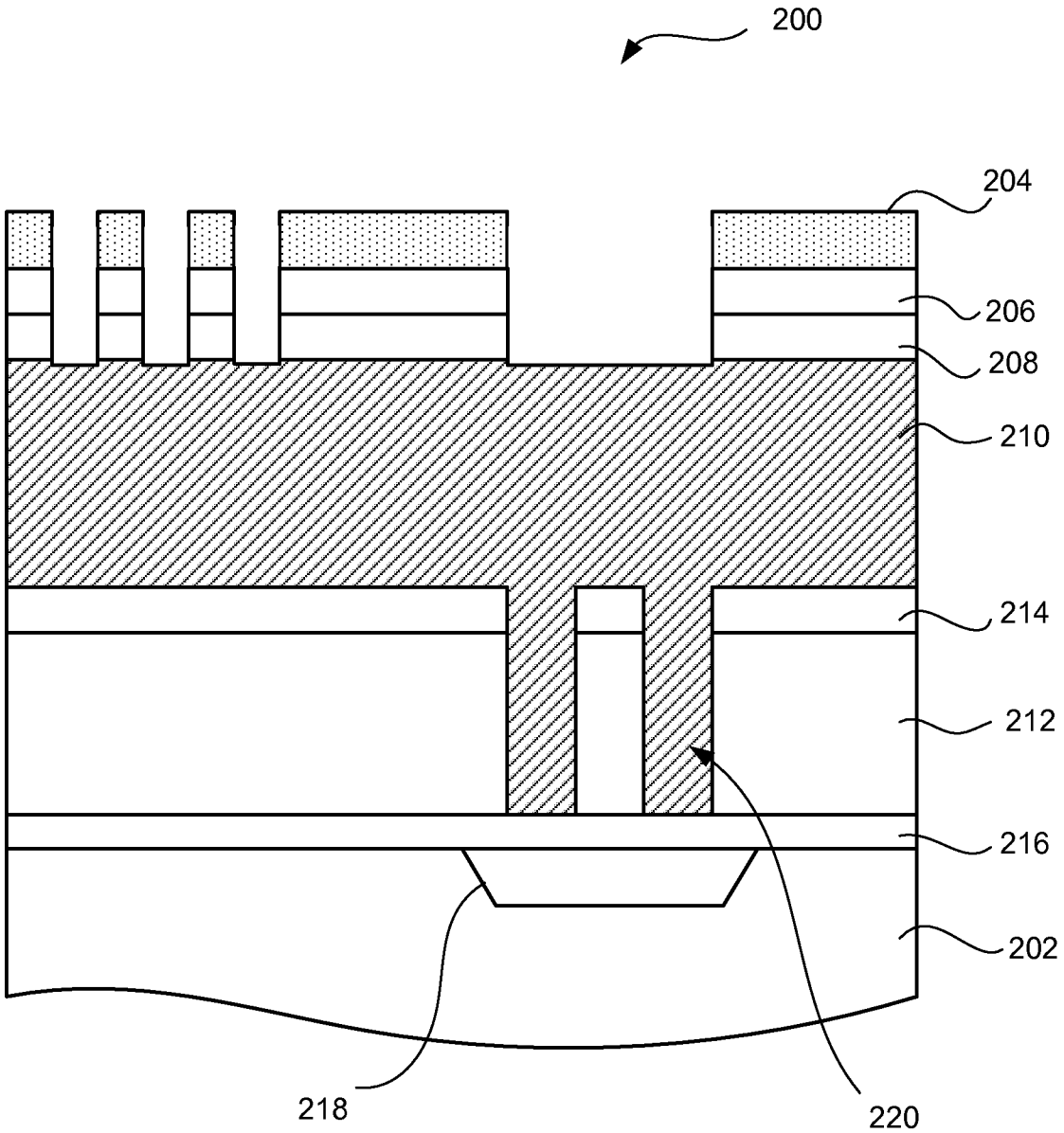


FIG. 2B

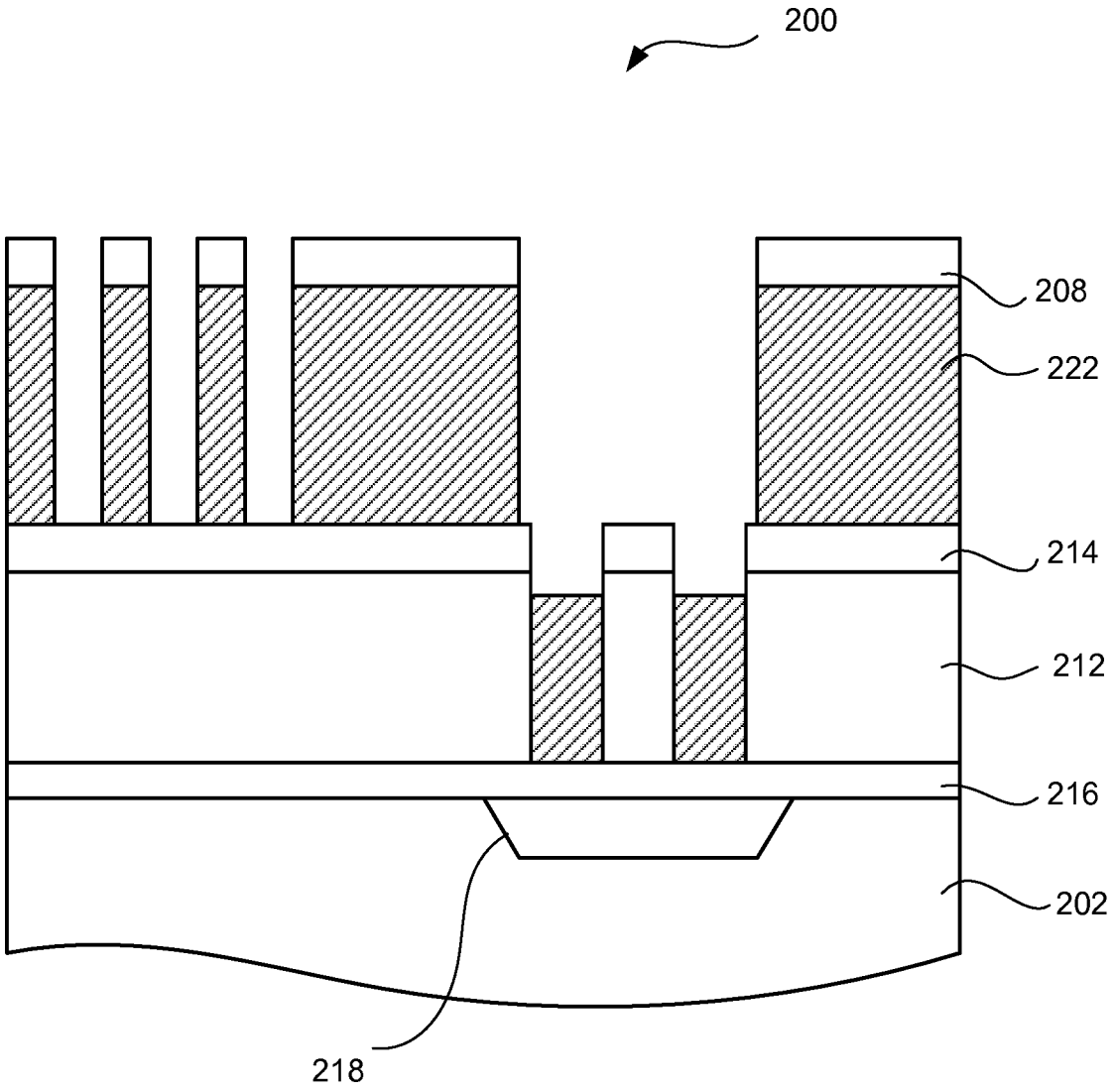


FIG. 2C

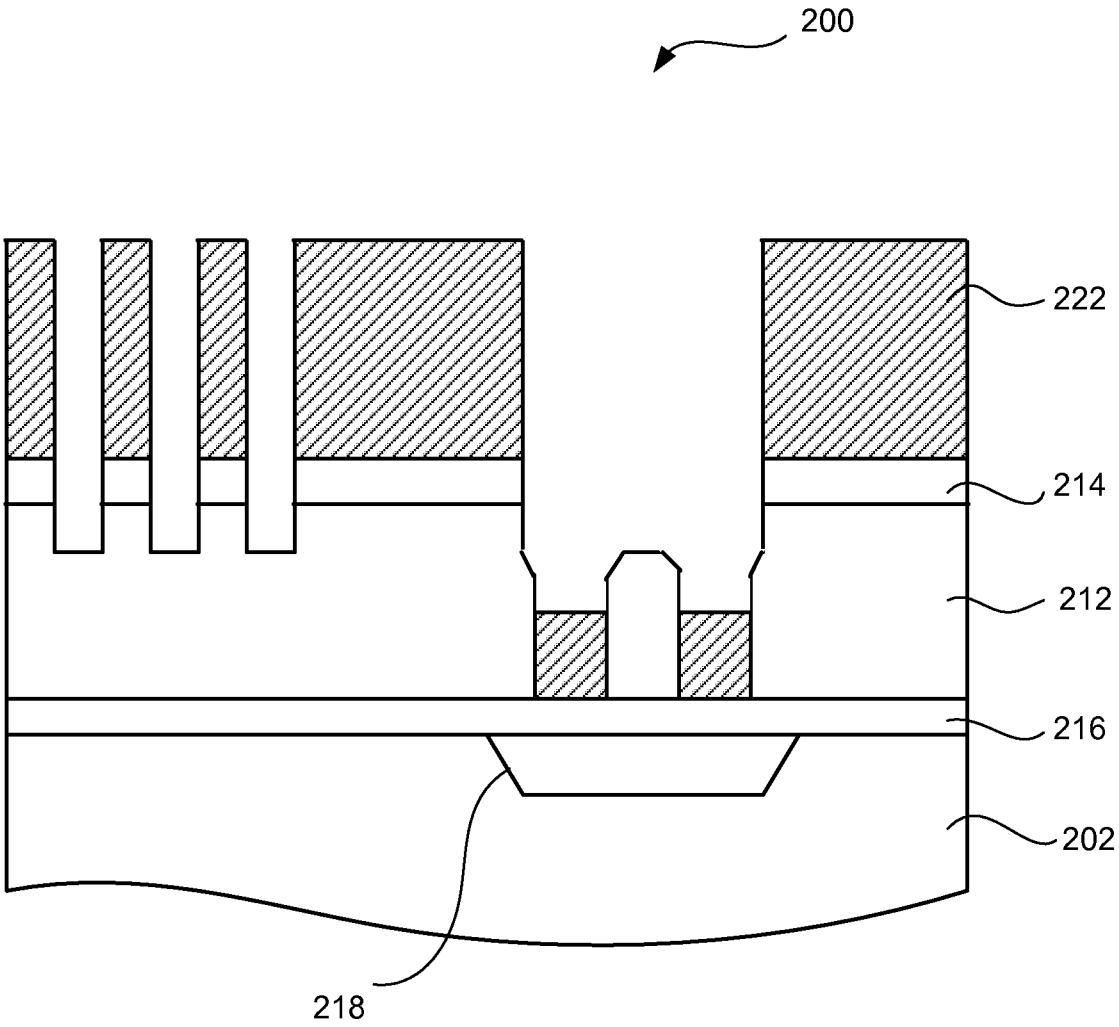


FIG. 2D

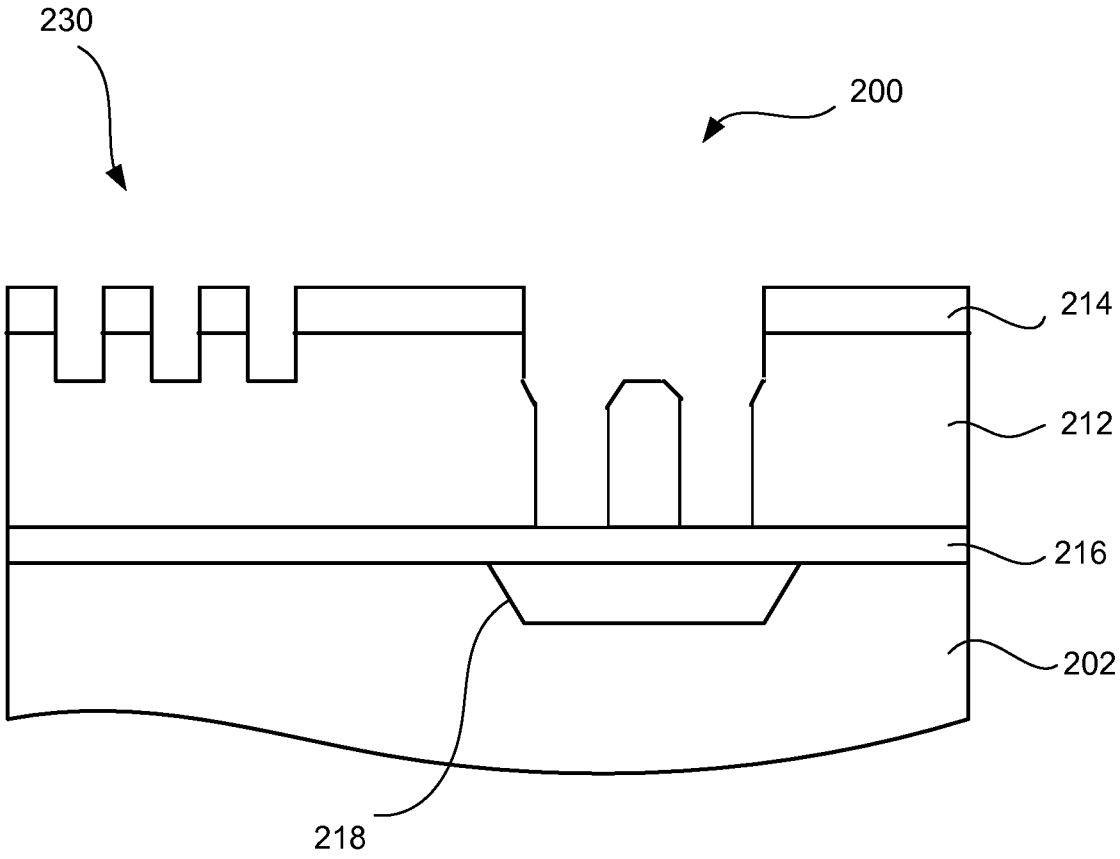


FIG. 2E

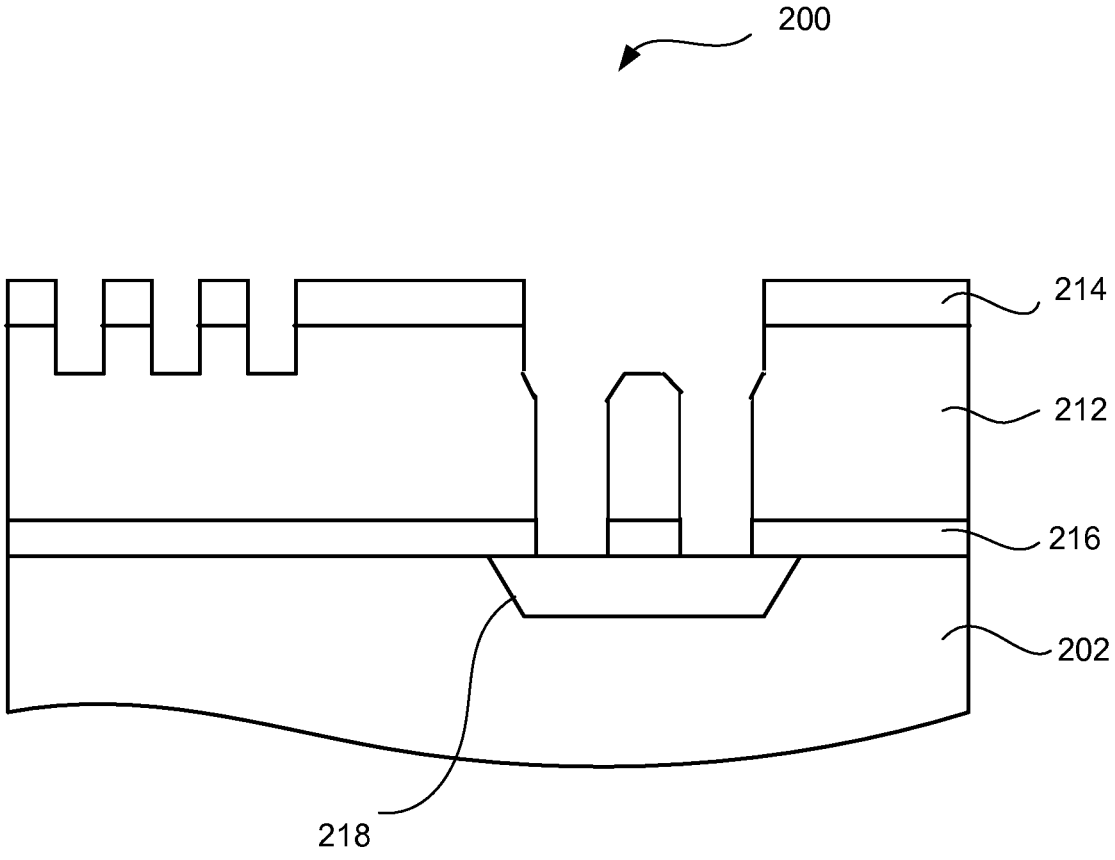


FIG. 2F

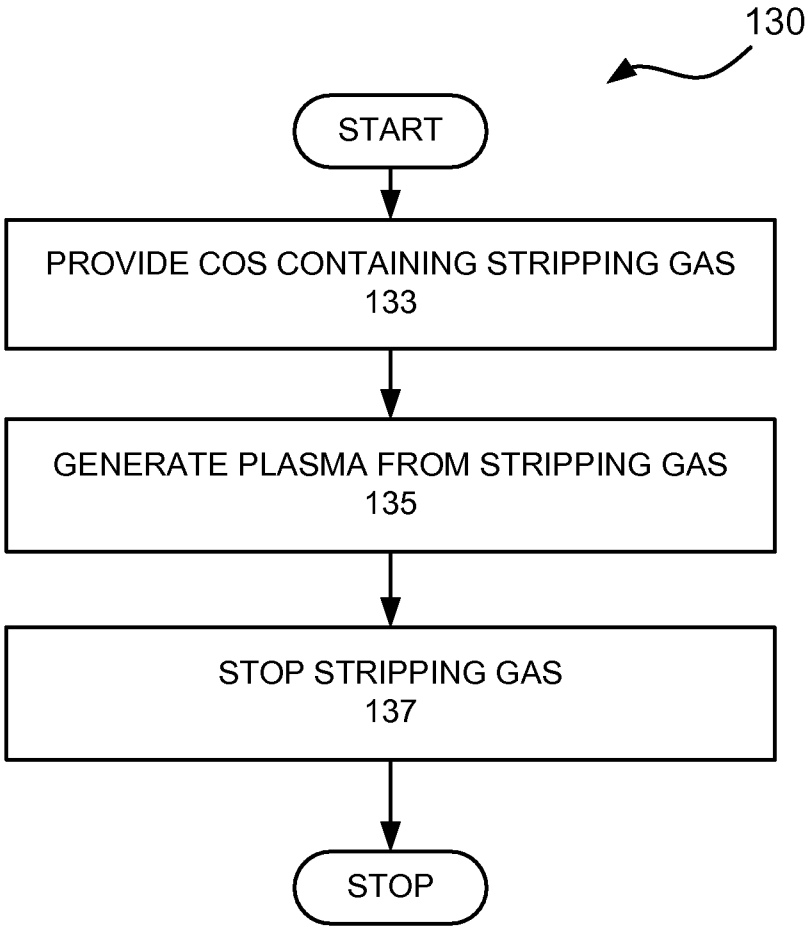

130
START
PROVIDE COS CONTAINING STRIPPING GAS
133
GENERATE PLASMA FROM STRIPPING GAS
135
STOP STRIPPING GAS
137
STOP

FIG. 3

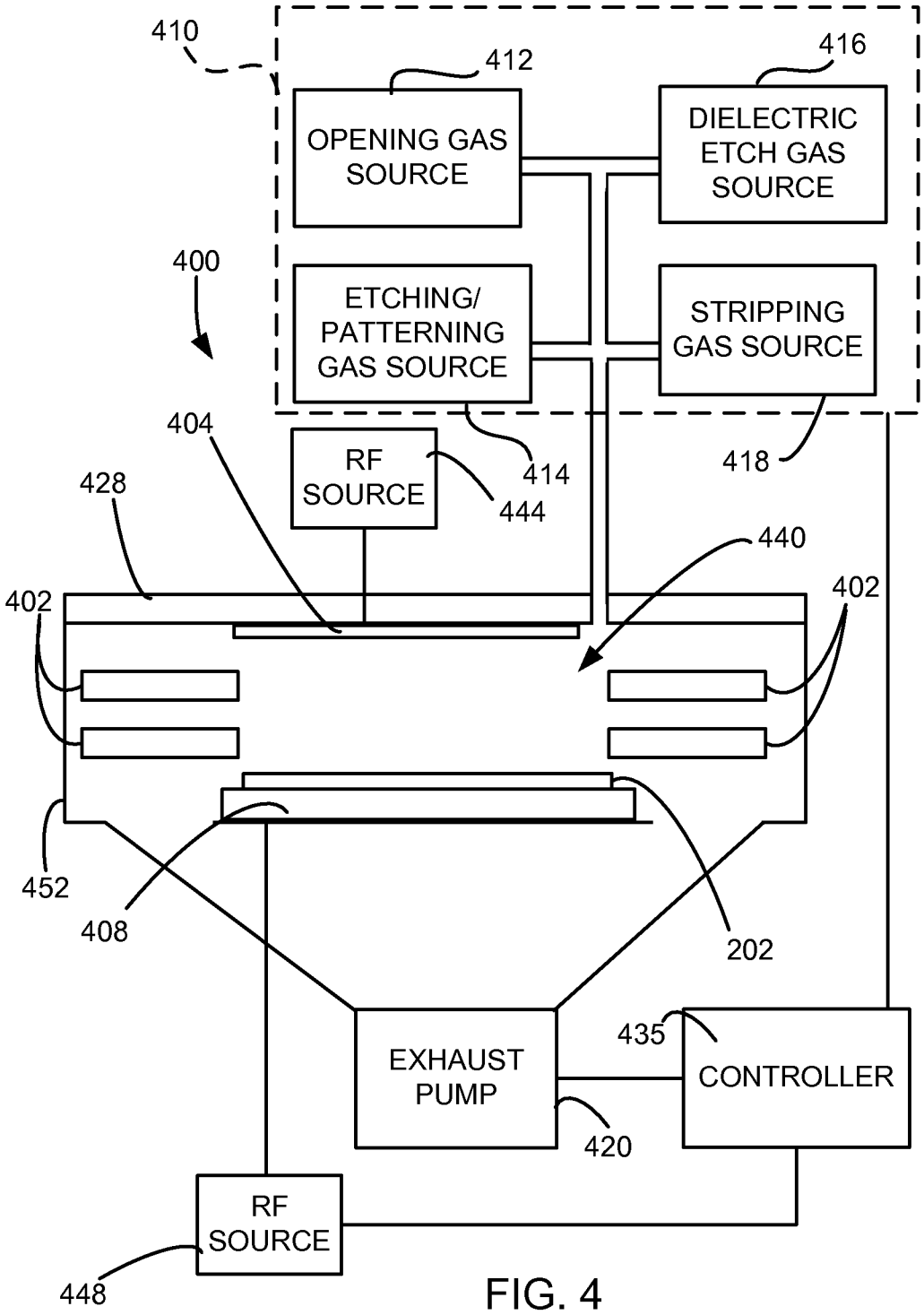

410
412
416
OPENING GAS SOURCE
DIELECTRIC ETCH GAS SOURCE
400
ETCHING/ PATTERNING GAS SOURCE
STRIPPING GAS SOURCE
404
RF SOURCE
414
418
444
428
440
402
402
452
408
202
435
EXHAUST PUMP
CONTROLLER
420
RF SOURCE
448

FIG. 4

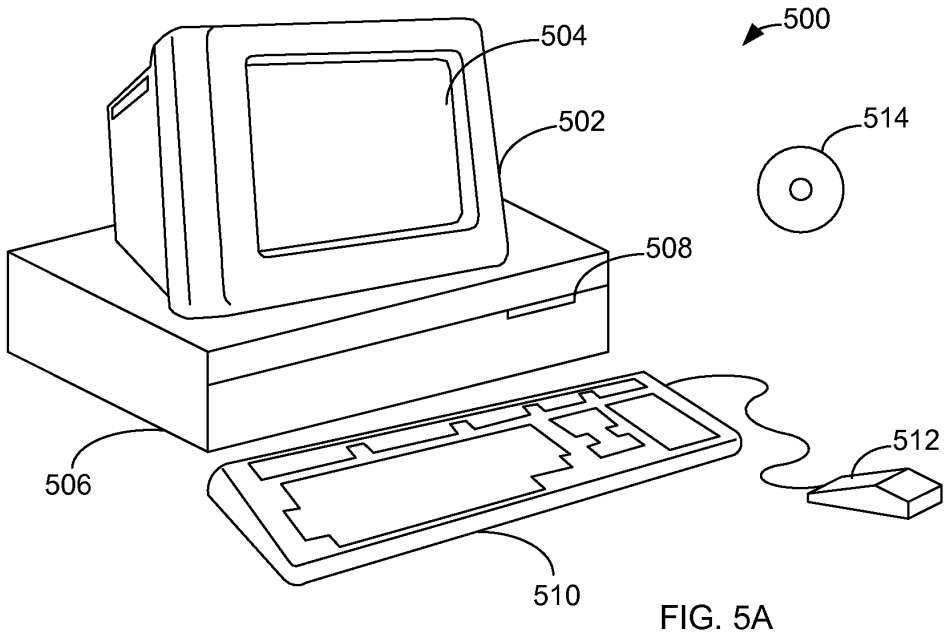

500
504
502
514
508
512
506
510

FIG. 5A

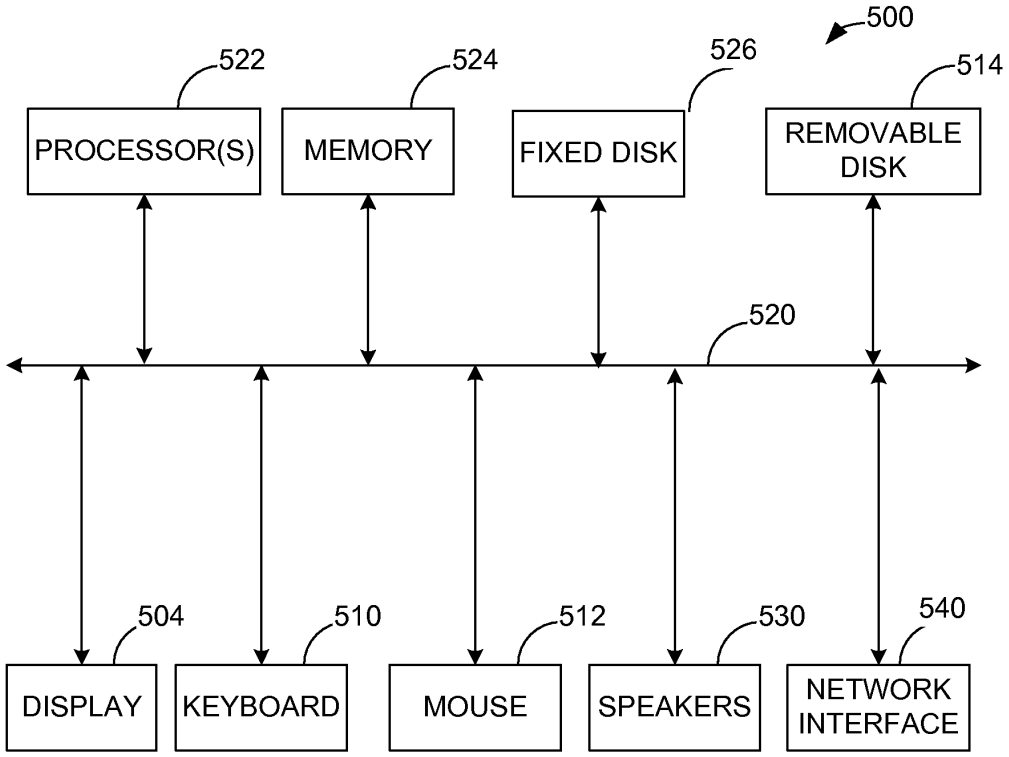

500
522
524
526
514
PROCESSOR(S)
MEMORY
FIXED DISK
REMOVABLE DISK
520
504
510
512
530
540
DISPLAY
KEYBOARD
MOUSE
SPEAKERS
NETWORK INTERFACE

FIG. 5B

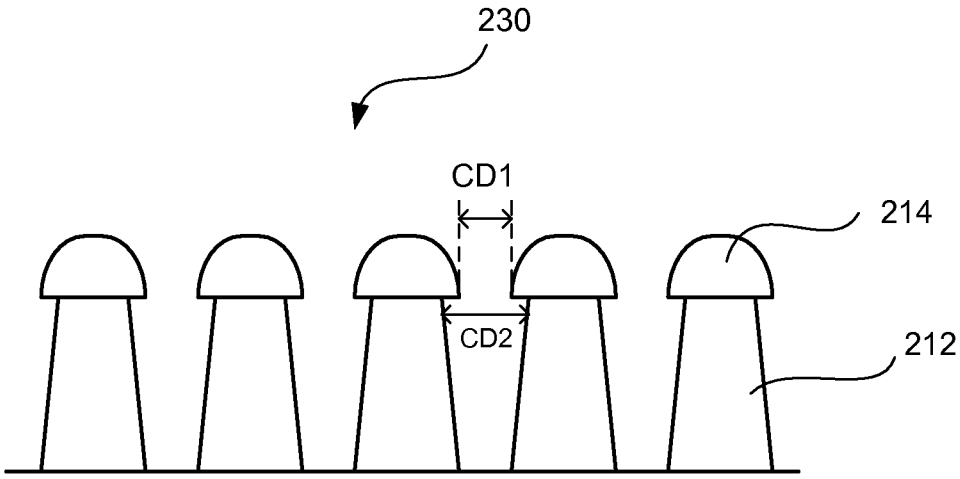


FIG. 6A

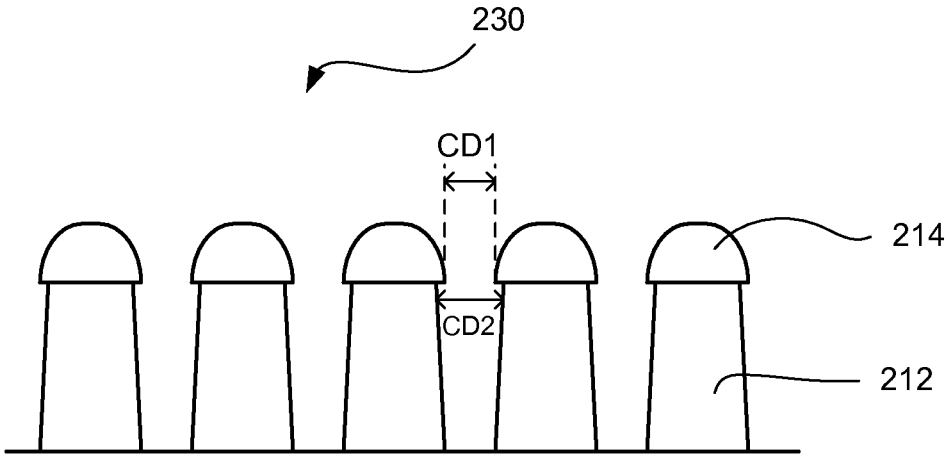


FIG. 6B